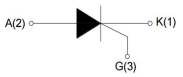
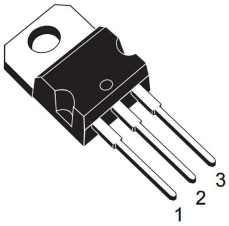
Silicon Controlled Rectifier series

1 Description

TYN612 series of silicon controlled rectifiers, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state



V_{RRM}/V_{DRM} =600/800
I_{GT} =≤15mA
$I_{T(RMS)}$ =12A



TO-220

2 Features

- High current output up to 12A
- Low Peak on-state voltage drop
- High voltage
- High reliability

3 Applications

- relay
- Motorcycle
- power charger
- T-tools etc

4 Electrical Characteristics

4.1 Absolute Maximum Ratings （Tc=25℃,unless otherwise noted）

PARAMETER		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (Tj=25℃)		V_{DRM}	600/800	V
Repetitive peak reverse voltage (Tj=25℃)		V_{RRM}	600/800	V
RMS on-state current		$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current	tp=8.3ms	I_{TSM}	130	A
	tp=10ms		120	
I^2t value for fusing (tp=10ms)		I^2t	72	A
Repetitive rate of rise of on-state current (IG=2×IGT)		$d_{IT/dt}$	50	A/us
Peak gate current		I_{GM}	2	A
Peak gate power		P_{GM}	5	W
Average gate power dissipation		$P_{G(AV)}$	0.5	W
Operating junction temperature range		T_J	- 40 ~ 150	℃
Storage junction temperature range		T_{STG}	- 40 ~ 150	℃

4.2 Thermal Characteristics

PARAMETER	SYMBOL	VALUE	UNIT
Thermal Resistance, Junction to Case-sink	R_{thJC}	1.7	℃/W

4.3 Electrical Characteristics (Tc=25℃,unless otherwise noted)

SYMBOL	PARAMETER	Test Conditions		Min	Typ	Max	Unit
I_{GT}	Triggering gate current	V_D=12V R_L=33Ω		-	3	15	mA
V_{GT}	Triggering gate voltage			-	0.8	1.5	V
V_{GD}	Non-triggering gate voltage	V_D=V_{DRM} T_j=125℃ R_L=3.3KΩ		0.2	-	-	V
I_L	Latching Current	I_G=1.2I_{GT}		-	13	40	mA
I_H	Holding Current	I_T=500mA		-	11	30	mA
dv/dt	Critical Rate of Rise of Off-state Voltage	V_D=2/3V_{DRM} Gate Open T_j=125℃		200	400	-	V/us
V_{TM}	Peak Forward On-State Voltage	I_{TM}=23A tp=380us		-	1.32	1.7	V
I_{DRM}	Maximum forward or reverse leakage current	V_D=V_{DRM} V_R=V_{RRM}	Tj=25℃	-	-	10	uA
I_{RRM}	Maximum reverse leakage current		Tj=125℃	-	-	500	uA

5 Typical characteristics diagrams

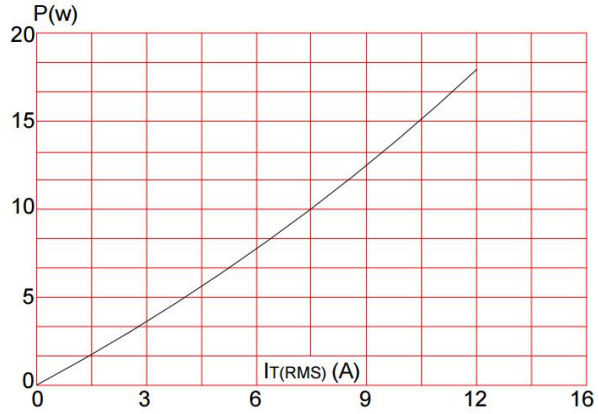


FIG.1: Maximum power dissipation versus RMS on-state current

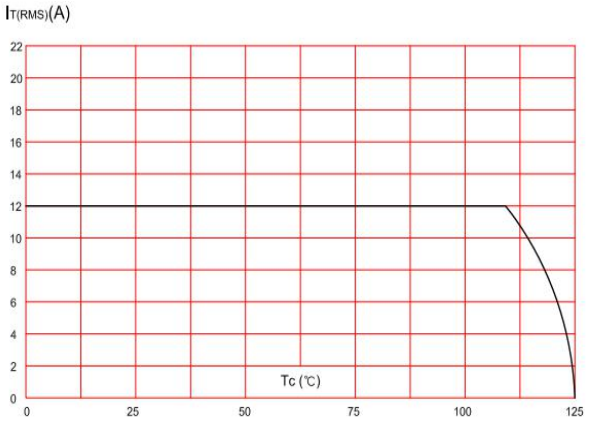


FIG.2: RMS on-state current versus case temperature

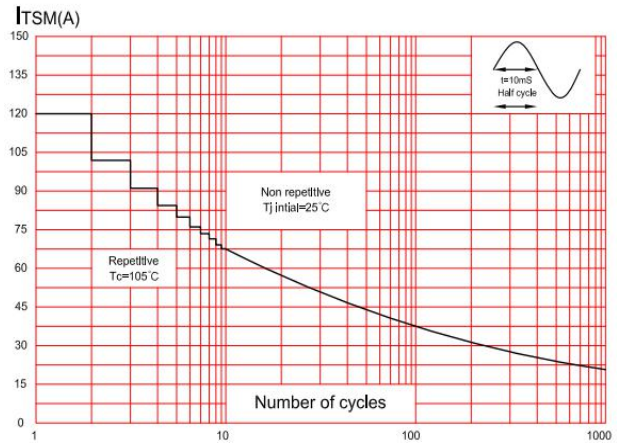


FIG.3: Surge peak on-state current versus number of cycles

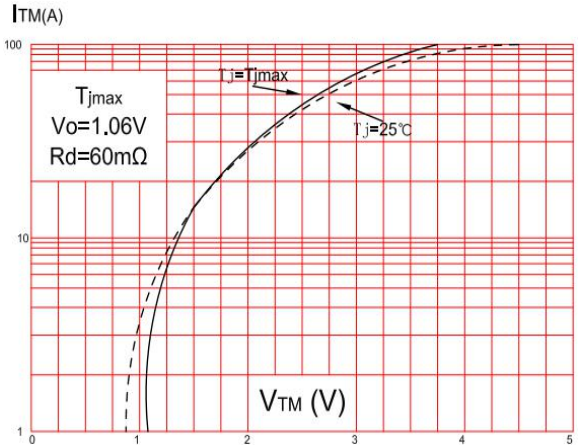


FIG.4: On-state characteristics (maximum values)

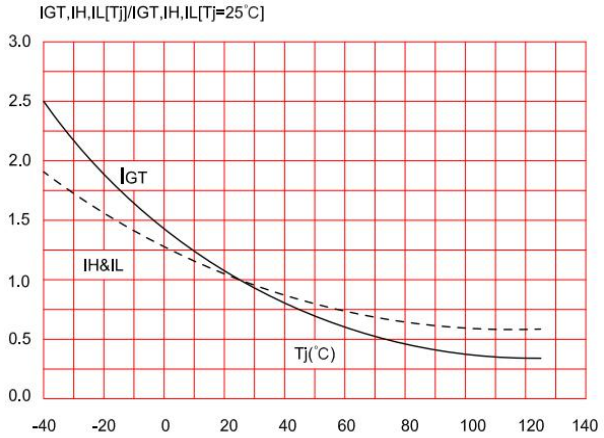
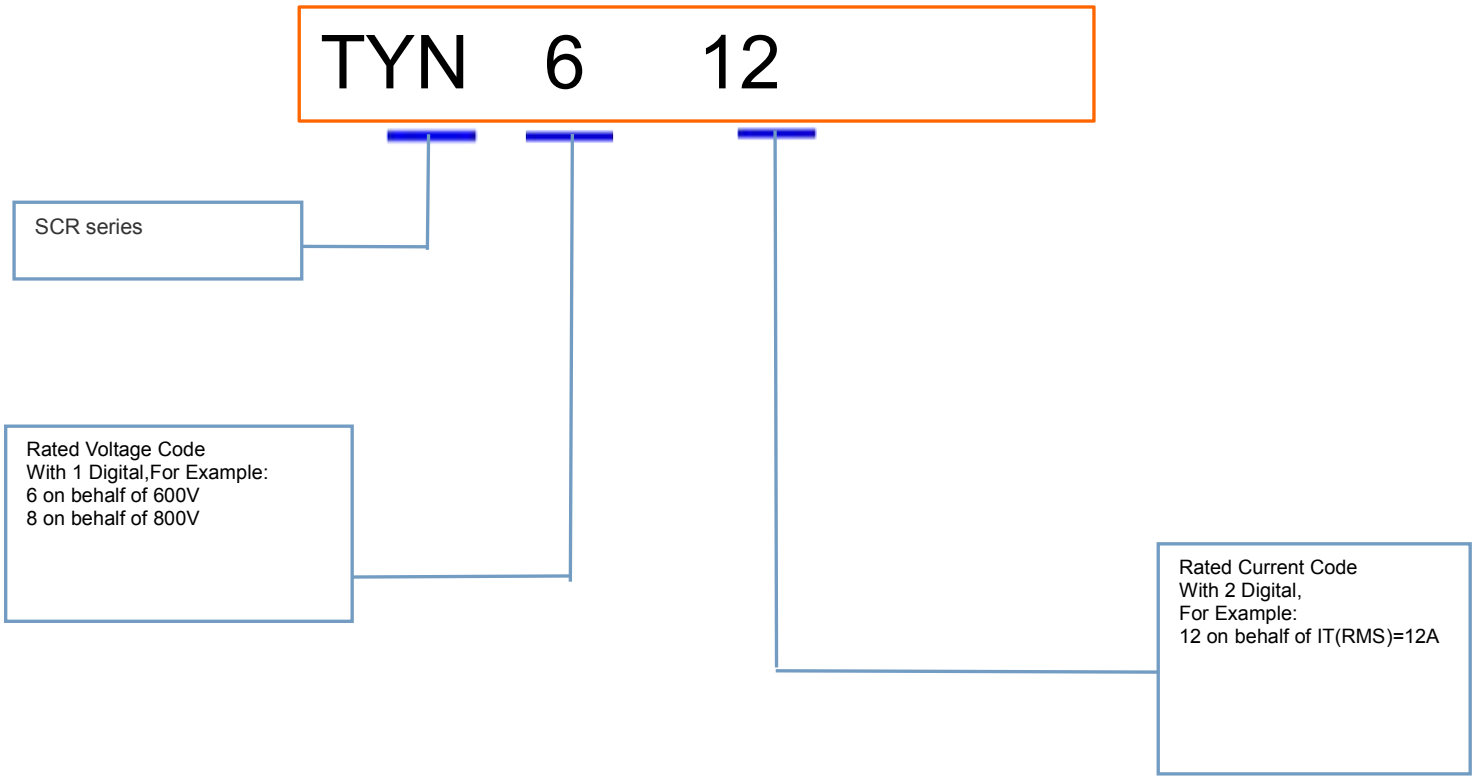


FIG.5: Relative variations of gate trigger current, holding current and latching current versus junction temperature

6 Product Names Rules

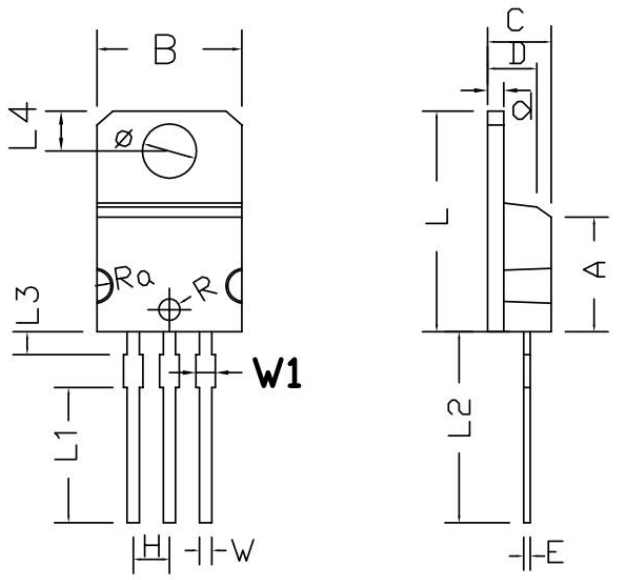


7 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
TYN612	TO-220	TYN612	Pb-free	Tube	1000//box

8 Dimensions

TO-220M PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
	MIN	MAX	MIN	MAX
A	8.03	8.05	0.316	0.317
B	10.13	10.23	0.399	0.403
C	4.42	4.52	0.174	0.178
D	3.42	3.52	0.135	0.139
E	0.44	0.46	0.017	0.018
L	15.25	15.45	0.601	0.609
H	2.52	2.56	0.099	0.101
W	0.85	0.87	0.033	0.034
Φ	3.78	3.82	0.149	0.151
R	0.74	0.76	0.029	0.030
Ra	9.44	9.48	0.372	0.374
d	1.28	1.32	0.050	0.052
L1	9.4	9.6	0.370	0.378
L2	13.22	13.62	0.521	0.537
L3	1.52	1.72	0.060	0.068
L4	2.7	2.9	0.106	0.114
W1	1.32	1.42	0.052	0.056

9 Attentions

- ROUM Semiconductor Technology CO.,LTD. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Roma products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

10 Appendix

Revision history:

Date	REV.	Description	Page
2017.08.19	1.0	Original	